

CLAIM AMENDMENTS

1 1. (currently amended) A chemical sensor having
2 comprising:
3 a substrate;
4 a first metallization plane arranged on [[a]] the
5 substrate; (1) and in which
6 an electrode structure (IDT) is formed in the first
7 metallization plane,
8 a passivation layer [[(6)]] applied to the first
9 metallization plane and structured formed with contact holes,
10 [[and]]
11 a chemical-sensitive ceramic layer [[(9)]] on the
12 passivation layer [[(6)]] and in the contact holes and capable of
13 changing electrical properties when contacted by predetermined
14 chemicals; and (7), characterized in that
15 a bond-promoting layer (8) is provided which is
16 configured as a second metallization plane and is located between
17 the passivation layer [[(6)]] and the ceramic layer [[(9)]].

1 2. (currently amended) The chemical sensor according to
2 claim 1 characterized in that wherein the second metallization
3 plane is so applied that it comes to lie in the contact holes
4 [[(7)]] upon the first metallization plane.

1 3. (currently amended) The chemical sensor according to
2 claim 1, ~~characterized in that a further comprising~~
3 ~~another~~ passivation layer (10) is located between the
4 bond-promoting layer 8 and the ceramic layer [[(9)]] and so
5 structured that the [[body]] bond-promoting layer [[(8)]] is
6 partially passivated.

1 4. (currently amended) The chemical sensor according to
2 claim 1 ~~characterized in that wherein two coplanar electrodes are~~
3 ~~formed~~ in the electrode structure [[(IDT)]] of the first
4 metallization plane, ~~two coplanar electrodes (IDT1, IDT2) are~~
5 ~~formed~~ by structuring and the second metallization plane does not
6 lie at a defined electrical potential.

1 5. (currently amended) The chemical sensor according to
2 claim 1 ~~characterized in that wherein~~ the electrode structure
3 [[(IDT)]] of the first metallization plane forms a first electrode
4 [[(IDT1)]] and the second metallization plane is configured as a
5 second electrode [[(IDT2)]] and lies at a defined electrical
6 potential so that the sensitive ceramic layer [[(9)]] is provided
7 with a vertical electrode.

1 6. (currently amended) The chemical sensor according to
2 claim 5 ~~1 characterized in that wherein the first and second~~
3 electrodes [[(IDT 1, IDT 2)]] are configured as interdigitating
4 electrodes.

1 7. (currently amended) The chemical sensor according to
2 claim 1 ~~characterized in that wherein a heating structure and a~~
3 ~~temperature-measuring structure are formed in the first~~
4 metallization plane [[,]] in addition to the electrode structure
5 (IDT) ~~a heating structure (4) and a temperature measuring structure~~
6 ~~(5) are formed.~~

1 8. (currently amended) The chemical sensor according to
2 claim 7 ~~1 characterized in that wherein the structures [[(4, 5,~~
3 IDT)]] of the first metallization plane are formed on the front
4 side of an Si-substrate [[(1)]] which has a membrane [[(3)]].

1 9. (currently amended) The chemical sensor according to
2 claim 1 ~~characterized in that wherein the material for the second~~
3 metallization plane is Au, Cr/Au, Pt, Pd, W or Sn.

1 10. (currently amended) The chemical sensor according
2 to claim 1 ~~characterized in that wherein the application of the~~
3 sensitive ceramic layer is effected by silk screening, dispenser
4 application or an ink jet process.